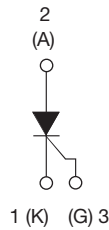
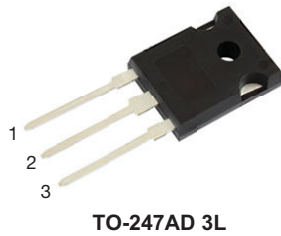


## Thyristor High Voltage, Phase Control SCR, 40 A



## FEATURES

- Low  $I_{GT}$
- AEC-Q101 qualified meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see [ekoweiss.semiconductors](http://ekoweiss.semiconductors)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## PRIMARY CHARACTERISTICS

|                       |                   |
|-----------------------|-------------------|
| $I_{T(AV)}$           | 35 A              |
| $V_{DRM}/V_{RRM}$     | 1200 V            |
| $V_{TM}$              | 1.45 V            |
| $I_{GT}$              | 150 mA            |
| $T_J$                 | -40 °C to +125 °C |
| Package               | TO-247AD 3L       |
| Circuit configuration | Single SCR        |

## APPLICATIONS

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

## DESCRIPTION

The EKS-40TPS12.. high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

## MAJOR RATINGS AND CHARACTERISTICS

| PARAMETER         | TEST CONDITIONS            | VALUES        | UNITS      |
|-------------------|----------------------------|---------------|------------|
| $I_{T(AV)}$       | Sinusoidal waveform        | 35            | A          |
| $I_{RMS}$         |                            | 55            |            |
| $V_{RRM}/V_{DRM}$ |                            | 1200          | V          |
| $I_{TSM}$         |                            | 600           | A          |
| $V_T$             | 40 A, $T_J = 25\text{ °C}$ | 1.45          | V          |
| dv/dt             |                            | 500           | V/ $\mu$ s |
| di/dt             |                            | 100           | A/ $\mu$ s |
| $T_J$             |                            | - 40 to + 125 | °C         |

## VOLTAGE RATINGS

| PART NUMBER     | $V_{RRM}/V_{DRM}$ , MAXIMUM<br>REPETITIVE PEAK AND<br>OFF-STATE VOLTAGE<br>V | $V_{RSM}$ , MAXIMUM<br>NON-REPETITIVE PEAK<br>REVERSE VOLTAGE<br>V | $I_{RRM}/I_{DRM}$<br>AT 125 °C<br>mA |
|-----------------|------------------------------------------------------------------------------|--------------------------------------------------------------------|--------------------------------------|
| EKS-40TPS12APBF | 1200                                                                         | 1300                                                               | 10                                   |

| ABSOLUTE MAXIMUM RATINGS                             |                                    |                                                                                                       |                                                           |        |                   |
|------------------------------------------------------|------------------------------------|-------------------------------------------------------------------------------------------------------|-----------------------------------------------------------|--------|-------------------|
| PARAMETER                                            | SYMBOL                             | TEST CONDITIONS                                                                                       |                                                           | VALUES | UNITS             |
| Maximum average on-state current                     | I <sub>T(AV)</sub>                 | T <sub>C</sub> = 79 °C, 180° conduction half sine wave                                                |                                                           | 35     | A                 |
| Maximum continuous RMS on-state current as AC switch | I <sub>T(RMS)</sub>                |                                                                                                       |                                                           | 55     |                   |
| Maximum peak, one-cycle non-repetitive surge current | I <sub>TSM</sub>                   | 10 ms sine pulse, rated V <sub>RRM</sub> applied                                                      | Initial<br>T <sub>J</sub> = T <sub>J</sub> max.           | 500    |                   |
|                                                      |                                    | 10 ms sine pulse, no voltage reapplied                                                                |                                                           | 600    |                   |
| Maximum I <sup>2</sup> t for fusing                  | I <sup>2</sup> t                   | 10 ms sine pulse, rated V <sub>RRM</sub> applied                                                      |                                                           | 1250   | A <sup>2</sup> s  |
|                                                      |                                    | 10 ms sine pulse, no voltage reapplied                                                                |                                                           | 1760   |                   |
| Maximum I <sup>2</sup> √t for fusing                 | I <sup>2</sup> √t                  | t = 0.1 ms to 10 ms, no voltage reapplied                                                             |                                                           | 17 600 | A <sup>2</sup> √s |
| Low level value of threshold voltage                 | V <sub>T(TO)1</sub>                | T <sub>J</sub> = 125 °C                                                                               |                                                           | 1.02   | V                 |
| High level value of threshold voltage                | V <sub>T(TO)2</sub>                |                                                                                                       |                                                           | 1.23   |                   |
| Low level value of on-state slope resistance         | r <sub>t1</sub>                    |                                                                                                       |                                                           | 9.74   | mΩ                |
| High level value of on-state slope resistance        | r <sub>t2</sub>                    |                                                                                                       |                                                           | 7.50   |                   |
| Maximum peak on-state voltage                        | V <sub>TM</sub>                    | 110 A, T <sub>J</sub> = 25 °C                                                                         |                                                           | 1.85   | V                 |
| Maximum rate of rise of turned-on current            | di/dt                              | T <sub>J</sub> = 25 °C                                                                                |                                                           | 100    | A/μs              |
| Maximum holding current                              | I <sub>H</sub>                     | Anode supply = 6 V, resistive load, initial T <sub>J</sub> = 1 A, I <sub>T</sub> = 25 °C              |                                                           | 300    | mA                |
| Maximum latching current                             | I <sub>L</sub>                     | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C                                            |                                                           | 350    |                   |
| Maximum reverse and direct leakage current           | I <sub>RRM</sub> /I <sub>DRM</sub> | T <sub>J</sub> = 25 °C                                                                                | V <sub>R</sub> = rated V <sub>RRM</sub> /V <sub>DRM</sub> | 0.5    |                   |
|                                                      |                                    | T <sub>J</sub> = 125 °C                                                                               |                                                           | 10     |                   |
| Maximum rate of rise of off-state voltage            | dv/dt                              | T <sub>J</sub> = T <sub>J</sub> maximum, linear to 80 % V <sub>DRM</sub> , R <sub>g</sub> - k = 100 Ω |                                                           | 500    | V/μs              |

| TRIGGERING                                  |                    |                                                         |                                      |        |       |
|---------------------------------------------|--------------------|---------------------------------------------------------|--------------------------------------|--------|-------|
| PARAMETER                                   | SYMBOL             | TEST CONDITIONS                                         |                                      | VALUES | UNITS |
| Maximum peak gate power                     | P <sub>GM</sub>    |                                                         |                                      | 10     | W     |
| Maximum average gate power                  | P <sub>G(AV)</sub> |                                                         |                                      | 2.5    |       |
| Maximum peak gate current                   | I <sub>GM</sub>    |                                                         |                                      | 2.5    | A     |
| Maximum peak negative gate voltage          | -V <sub>GM</sub>   |                                                         |                                      | 10     | V     |
| Maximum required DC gate voltage to trigger | V <sub>GT</sub>    | T <sub>J</sub> = - 40 °C                                | Anode supply = 6 V<br>resistive load | 2.0    | V     |
|                                             |                    | T <sub>J</sub> = 25 °C                                  |                                      | 1.7    |       |
|                                             |                    | T <sub>J</sub> = 125 °C                                 |                                      | 1.3    |       |
| Maximum required DC gate current to trigger | I <sub>GT</sub>    | T <sub>J</sub> = - 40 °C                                | Anode supply = 6 V<br>resistive load | 150    | mA    |
|                                             |                    | T <sub>J</sub> = 25 °C                                  |                                      | 40     |       |
|                                             |                    | T <sub>J</sub> = 125 °C                                 |                                      | 20     |       |
| Maximum DC gate voltage not to trigger      | V <sub>GD</sub>    | T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value |                                      | 0.15   | V     |
| Maximum DC gate current not to trigger      | I <sub>GD</sub>    |                                                         |                                      | 1      | mA    |

| THERMAL AND MECHANICAL SPECIFICATIONS           |                |                                      |               |            |
|-------------------------------------------------|----------------|--------------------------------------|---------------|------------|
| PARAMETER                                       | SYMBOL         | TEST CONDITIONS                      | VALUES        | UNITS      |
| Maximum junction and storage temperature range  | $T_J, T_{Stg}$ |                                      | - 40 to + 125 | °C         |
| Maximum thermal resistance, junction to case    | $R_{thJC}$     | DC operation                         | 0.6           | °C/W       |
| Maximum thermal resistance, junction to ambient | $R_{thJA}$     |                                      | 40            |            |
| Maximum thermal resistance, case to heat sink   | $R_{thCS}$     | Mounting surface, smooth and greased | 0.20          |            |
| Approximate weight                              |                |                                      | 6             | g          |
|                                                 |                |                                      | 0.21          | oz.        |
| Mounting torque                                 | minimum        |                                      | 6 (5)         | kgf · cm   |
|                                                 | maximum        |                                      | 12 (10)       | (lbf · in) |
| Marking device                                  |                | Case style TO-247AD 3L               | 40TPS12APBF   |            |

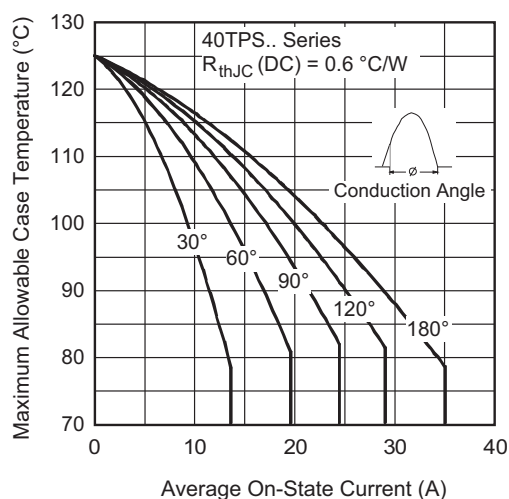


Fig. 1 - Current Rating Characteristics

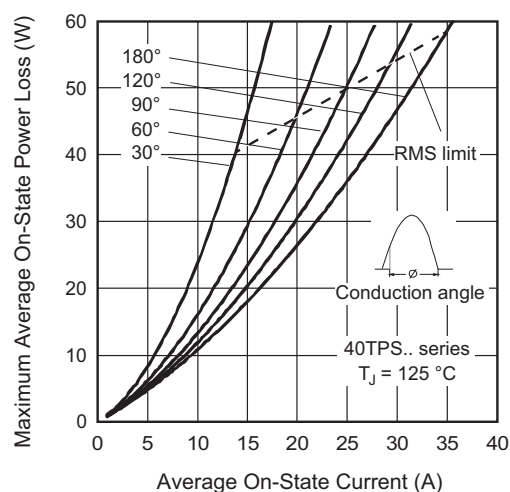


Fig. 3 - On-State Power Loss Characteristics

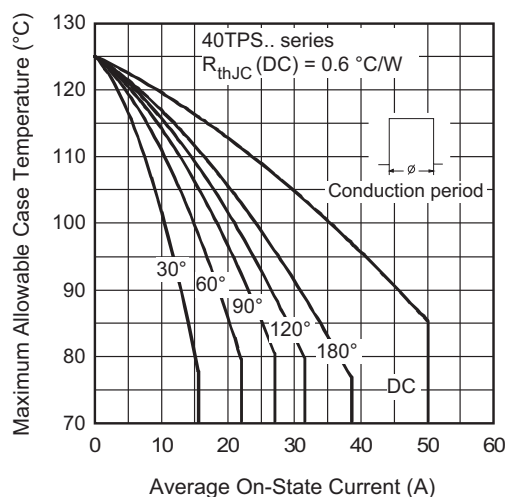


Fig. 2 - Current Rating Characteristics

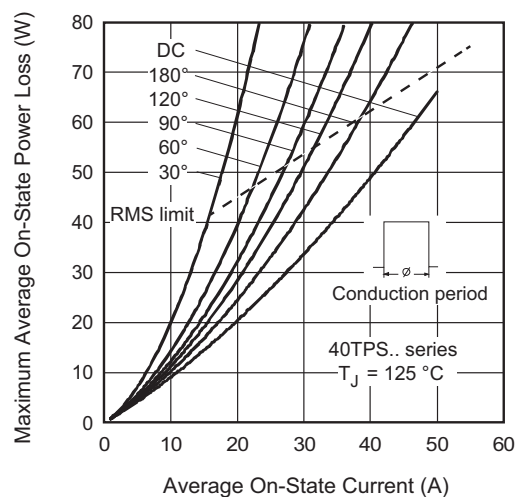


Fig. 4 - On-State Power Loss Characteristics

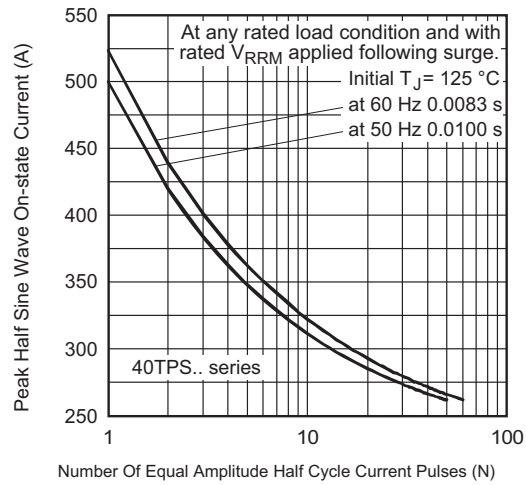


Fig. 5 - Maximum Non-Repetitive Surge Current

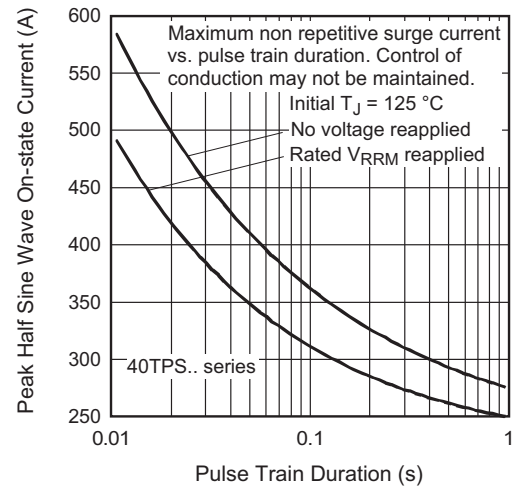


Fig. 6 - Maximum Non-Repetitive Surge Current

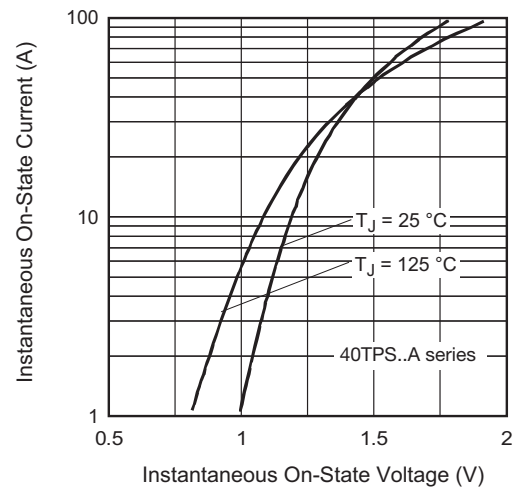


Fig. 7 - On-State Voltage Drop Characteristics

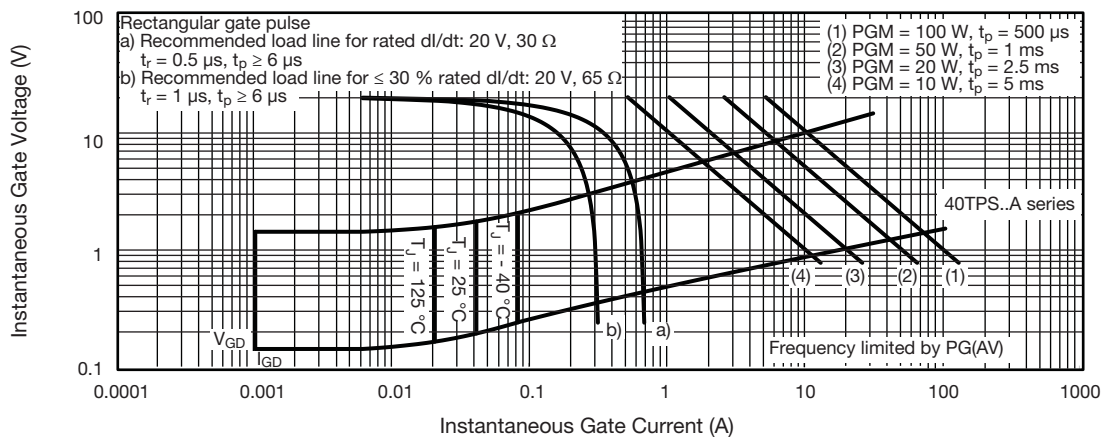


Fig. 8 - Gate Characteristics

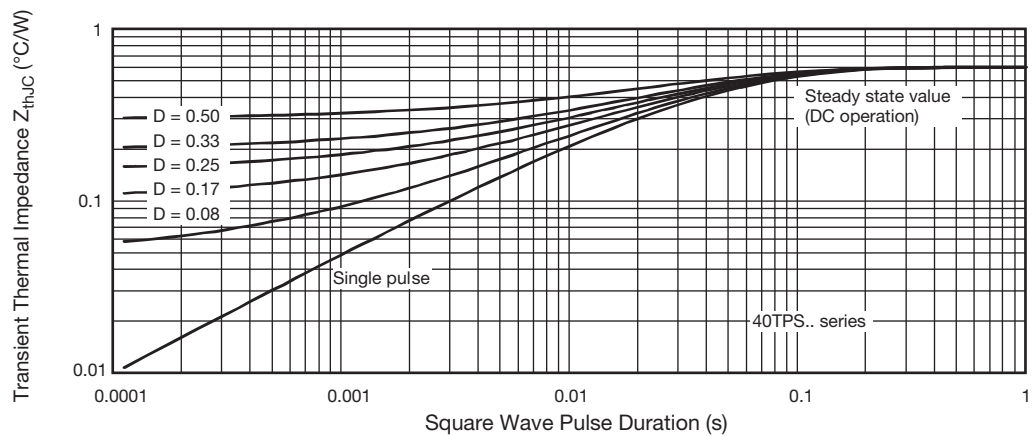


Fig. 9 - Thermal Impedance  $Z_{thJC}$  Characteristics

ORDERING INFORMATION TABLE

| Device code | EKS- | 40 | T | P | S | 12 | A | P | B | F  |
|-------------|------|----|---|---|---|----|---|---|---|----|
|             | 1    | 2  | 3 | 4 | 5 | 6  | 7 | 8 | 9 | 10 |

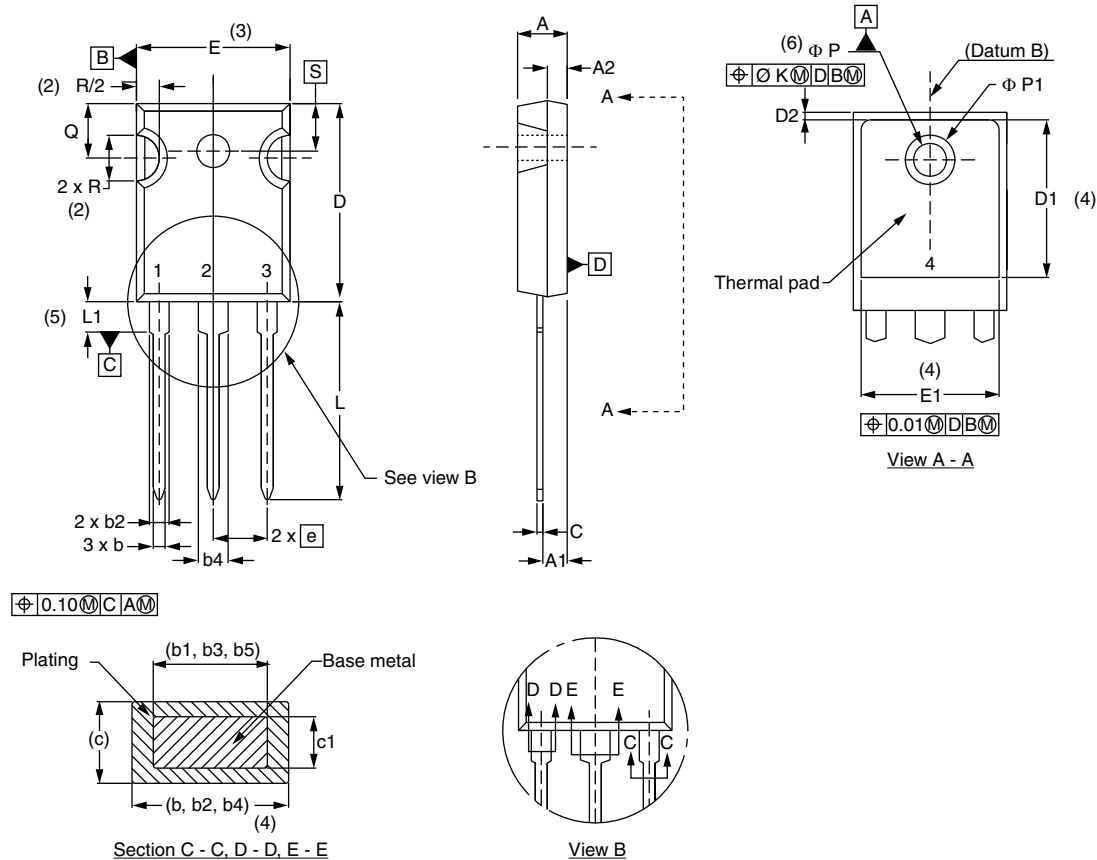
  

|    |   |                                                                                                                           |             |
|----|---|---------------------------------------------------------------------------------------------------------------------------|-------------|
| 1  | - | Ekoweiss Semiconductors product                                                                                           |             |
| 2  | - | Current rating (40 = 40 A)                                                                                                |             |
| 3  | - | Circuit configuration:<br>T = thyristor                                                                                   |             |
| 4  | - | Package:<br>P = TO-247                                                                                                    |             |
| 5  | - | Type of silicon:<br>S = standard recovery rectifier                                                                       |             |
| 6  | - | Voltage ratings                                                                                                           | 12 = 1200 V |
| 7  | - | <ul style="list-style-type: none"><li>A = Low Igt selection 40 mA maximum</li><li>None = standard Igt selection</li></ul> |             |
| 8  | - | P = long leads                                                                                                            |             |
| 9  | - | B = AEC-Q101 qualified                                                                                                    |             |
| 10 | - | Environmental digit:<br>F= halogen-free, RoHS-compliant, and terminations lead (Pb)-free                                  |             |

| ORDERING INFORMATION (Example) |                   |                        |                          |
|--------------------------------|-------------------|------------------------|--------------------------|
| PREFERRED P/N                  | QUANTITY PER TUBE | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION    |
| EKS-40TPS12APBF                | 30                | 450                    | Antistatic plastic tubes |

| LINKS TO RELATED DOCUMENTS |                                         |
|----------------------------|-----------------------------------------|
| Dimensions                 | <a href="#">EKOWEISS Semiconductors</a> |
| Part marking information   | <a href="#">EKOWEISS Semiconductors</a> |

## TO-247AD 3L

**DIMENSIONS** in millimeters and inches

| SYMBOL | MILLIMETERS |       | INCHES |       | NOTES |
|--------|-------------|-------|--------|-------|-------|
|        | MIN.        | MAX.  | MIN.   | MAX.  |       |
| A      | 4.65        | 5.31  | 0.183  | 0.209 |       |
| A1     | 2.21        | 2.59  | 0.087  | 0.102 |       |
| A2     | 1.50        | 2.49  | 0.059  | 0.098 |       |
| b      | 0.99        | 1.40  | 0.039  | 0.055 |       |
| b1     | 0.99        | 1.35  | 0.039  | 0.053 |       |
| b2     | 1.65        | 2.39  | 0.065  | 0.094 |       |
| b3     | 1.65        | 2.34  | 0.065  | 0.092 |       |
| b4     | 2.59        | 3.43  | 0.102  | 0.135 |       |
| b5     | 2.59        | 3.38  | 0.102  | 0.133 |       |
| c      | 0.38        | 0.89  | 0.015  | 0.035 |       |
| c1     | 0.38        | 0.84  | 0.015  | 0.033 |       |
| D      | 19.71       | 20.70 | 0.776  | 0.815 | 3     |
| D1     | 13.08       | -     | 0.515  | -     | 4     |

| SYMBOL    | MILLIMETERS |       | INCHES    |       | NOTES |
|-----------|-------------|-------|-----------|-------|-------|
|           | MIN.        | MAX.  | MIN.      | MAX.  |       |
| D2        | 0.51        | 1.30  | 0.020     | 0.051 |       |
| E         | 15.29       | 15.87 | 0.602     | 0.625 | 3     |
| E1        | 13.46       | -     | 0.53      | -     |       |
| e         | 5.46 BSC    |       | 0.215 BSC |       |       |
| $\phi K$  | 0.254       |       | 0.010     |       |       |
| L         | 19.81       | 20.32 | 0.780     | 0.800 |       |
| L1        | 3.71        | 4.29  | 0.146     | 0.169 |       |
| $\phi P$  | 3.56        | 3.66  | 0.14      | 0.144 |       |
| $\phi P1$ | -           | 6.98  | -         | 0.275 |       |
| Q         | 5.31        | 5.69  | 0.209     | 0.224 |       |
| R         | 4.52        | 5.49  | 0.178     | 0.216 |       |
| S         | 5.51 BSC    |       | 0.217 BSC |       |       |

**Notes**

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6)  $\phi P$  to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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